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### U.S. PATENT DOCUMENTS

EXAMINEE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.						
B.						
C.						
D.						
E.						
F.						
G.						
H.						
I.						

### FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES      NO
J.						
K.						
L.						
M.						
N.						
O.						

### OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

P.	Robert M. Wallace, "Challenges for the Characterization and Integration of High-k Gate Dielectrics," pp. 1-50, Nov. 2002, <a href="http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf">http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf</a>
Q.	Gerry Lucovsky, "The Physics and Chemistry of High-k Dielectrics and their Interfaces," pp. 1-49, available on June 2003, at <a href="http://www.sematech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf">http://www.sematech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf</a>
R.	
S.	
T.	

EXAMINER: *Michelle Otiada* DATE CONSIDERED: *9/27/04*

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.